

Lino Visser<sup>1\*</sup>, Niels Focke<sup>1\*</sup>, Spandan Anupam<sup>1</sup>, Vincent Mourik<sup>1</sup>

<sup>1</sup>JARA-FIT Institute for Quantum Information, Forschungszentrum Jülich GmbH and RWTH Aachen University

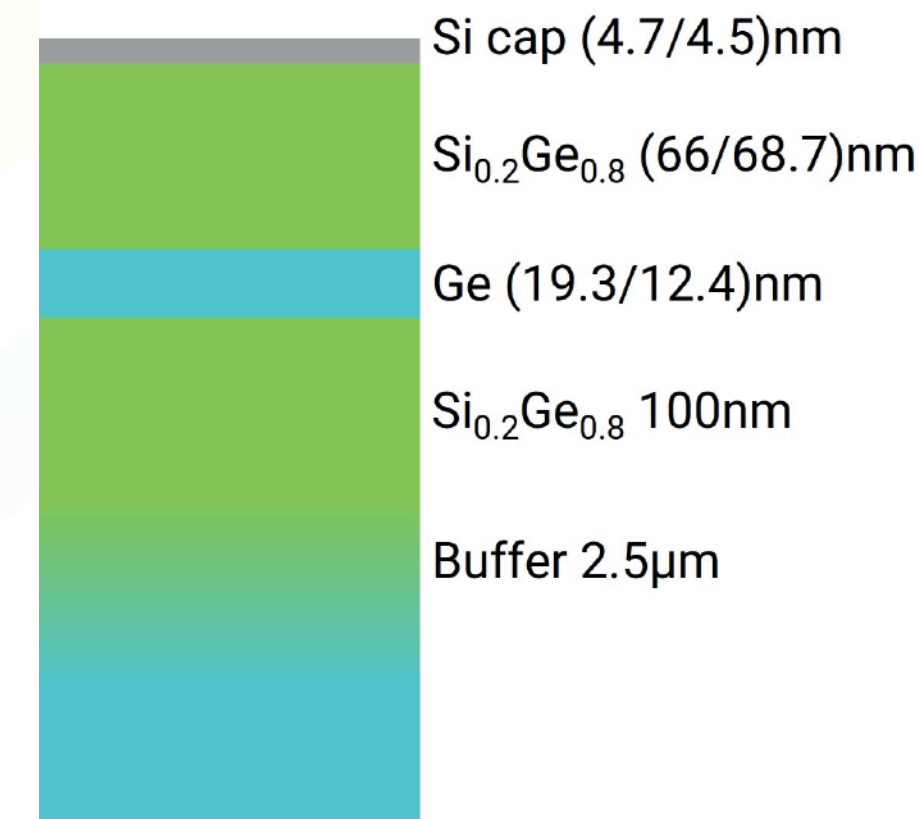
Felix Reichmann<sup>3</sup>, Alberto Mistrini<sup>3</sup>, Yuji Yamamoto<sup>3</sup>, Giovanni Capellini<sup>3,4</sup>, Marvin H. Zoellner<sup>3</sup>

<sup>3</sup>IHP, Leibniz-Institut für Innovative Mikroelektronik

<sup>4</sup>Dipartimento di Scienze, Università Roma Tre

## LAB INFRASTRUCTURE AND MOTIVATION

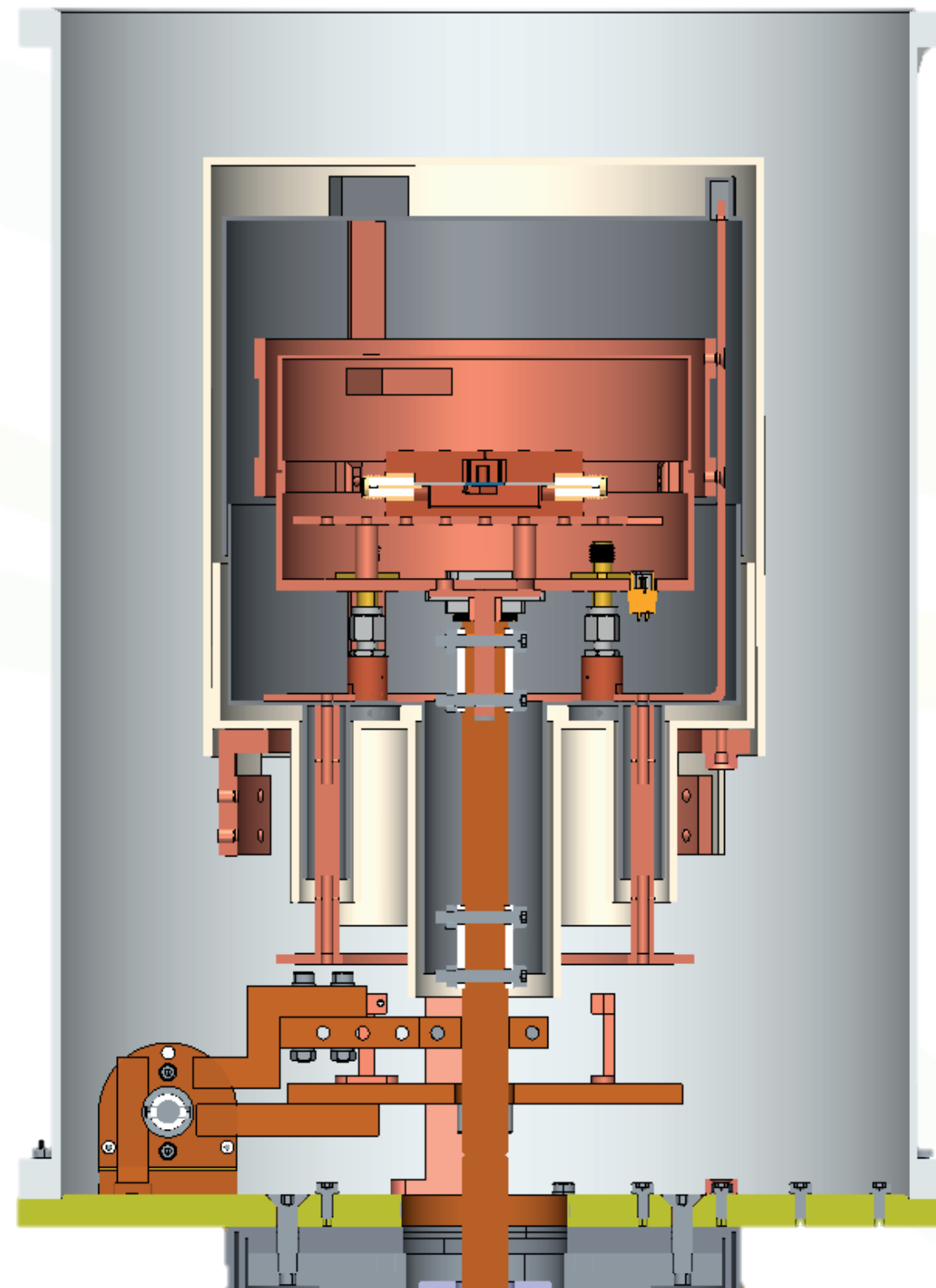
- Newly funded research group at FZ Jülich
- Investigate spin qubits and super-semi devices in Germanium quantum wells
- Growth of heterostructures done at Leibniz IHP
- Access to state-of-the-art cleanroom in FZJ<sup>[1]</sup> with our own AJA deposition tool
- Two Bluefors dilution refrigerators and one Entropy adiabatic demagnetization refrigerator (ADR)



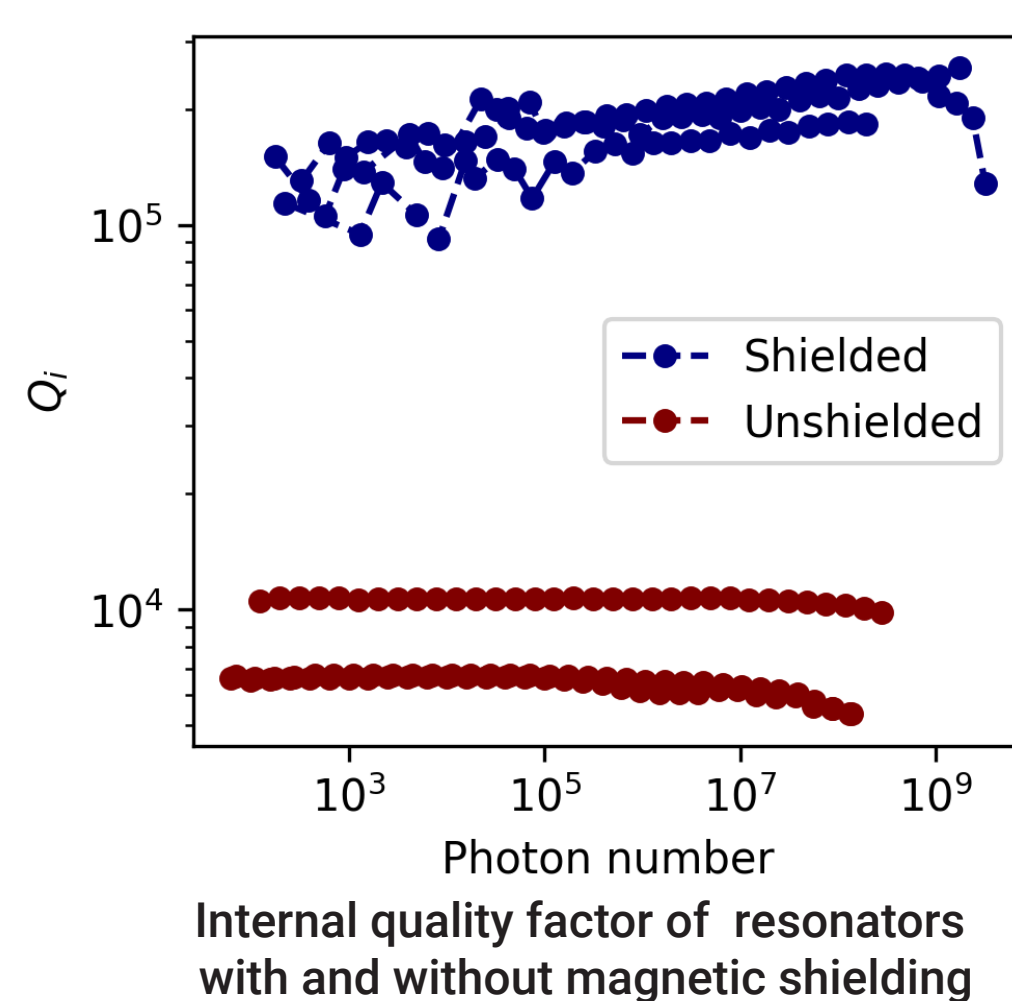
Layer stack of the two wafers investigated (wafer 1/wafer 2)

## CUSTOM SAMPLE SHIELDING IN AN ADR

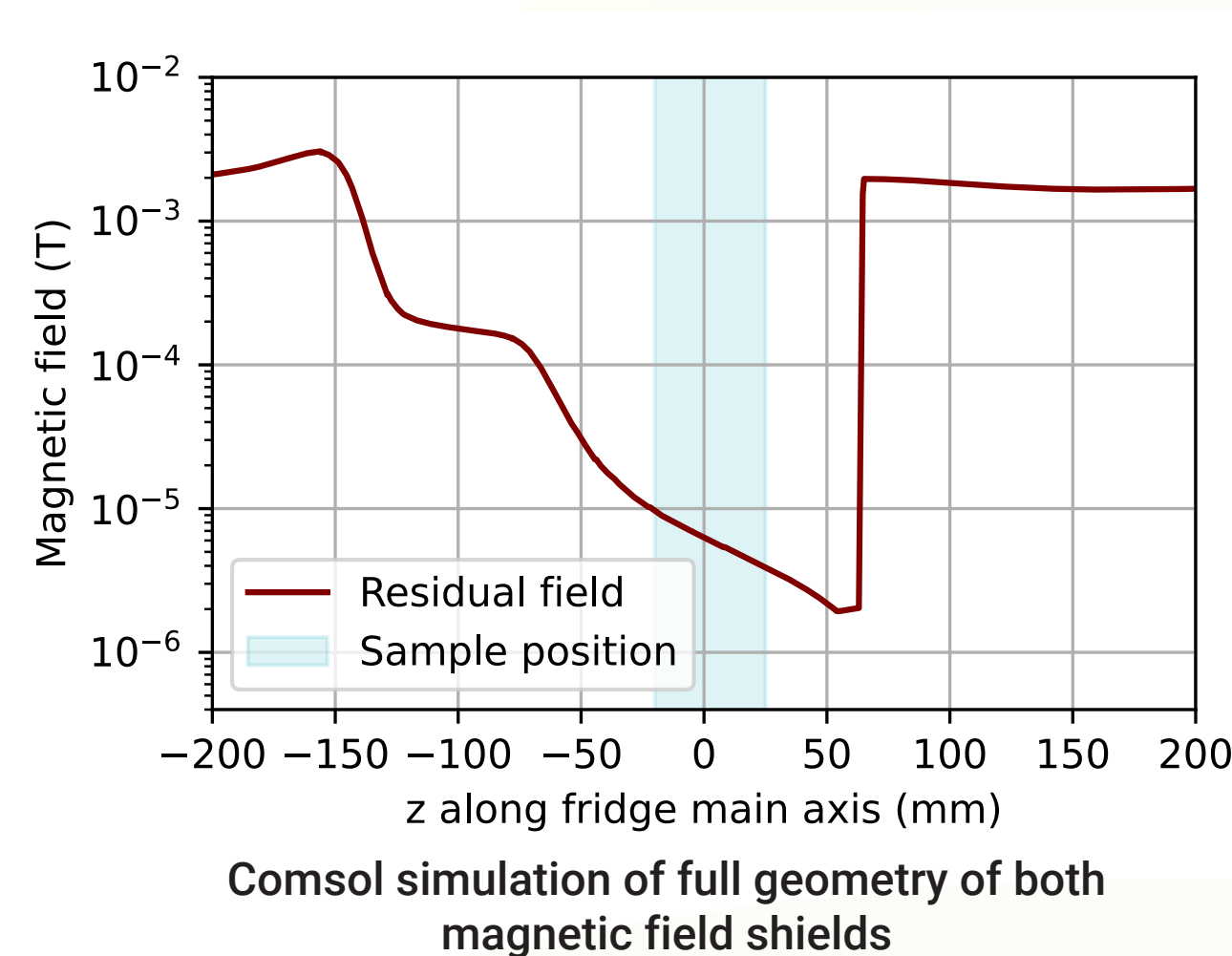
- Resonators studied together with Marc Neis and Rami Barends from PGI-13, FZ Jülich
- $\mu$ -metal and Niobium shields<sup>[2]</sup> coupled to 4K stage (PT cooled)
- Feedthrough for 4 RF lines & 48 DC lines
- Light-tight Radiation shield<sup>[3]</sup> coupled to lowest temperature stage
- Comsol simulations used to simulate shielding factor ( $B_{res}/B_0 > 100$  at sample)
- Chimneys to compensate feedthroughs
- Significantly increased resonator quality factors (Nb resonators on Si) with magnetic shielding



Schematic cross-section of mounted shields



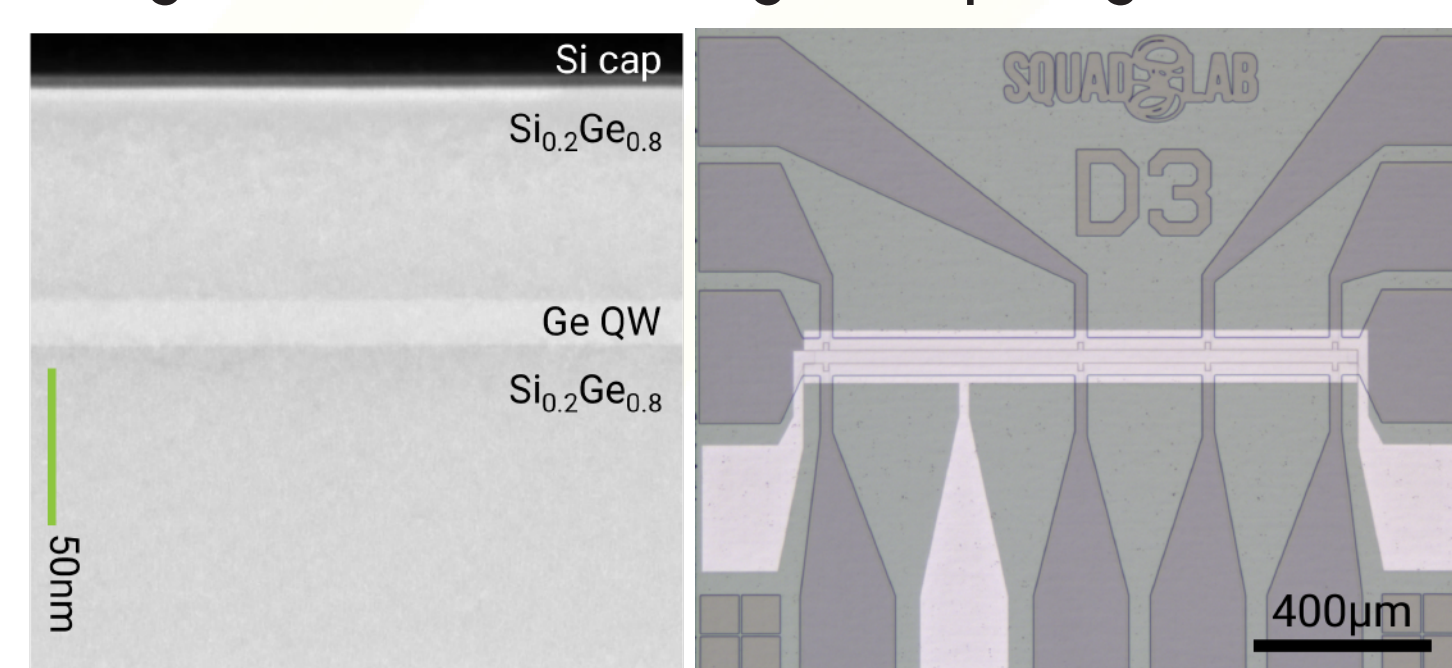
Internal quality factor of resonators with and without magnetic shielding



Comsol simulation of full geometry of both magnetic field shields

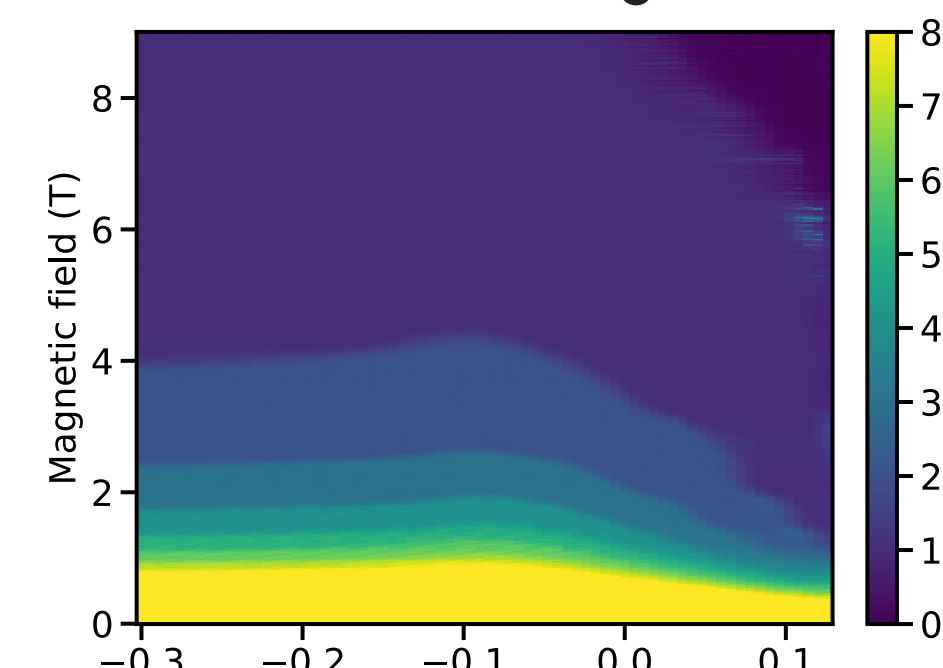
## HETEROSTRUCTURE OPTIMIZATION

- Feedback loop with IHP
- Screening gates to compensate always-on wafers
- Edge currents or charged cap might lead to kink in Landau fan diagram

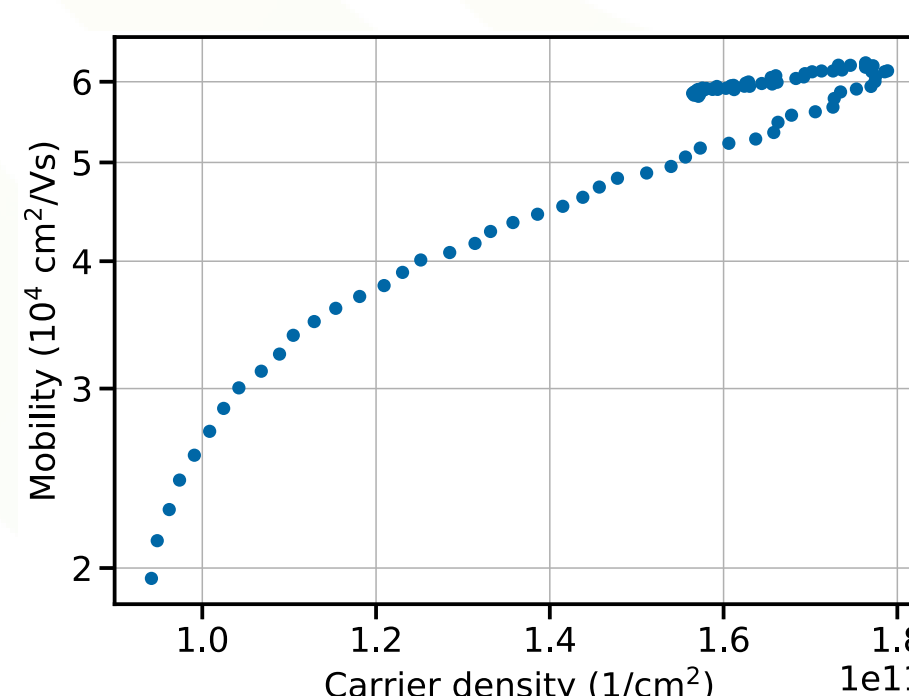


TEM image of wafer 2

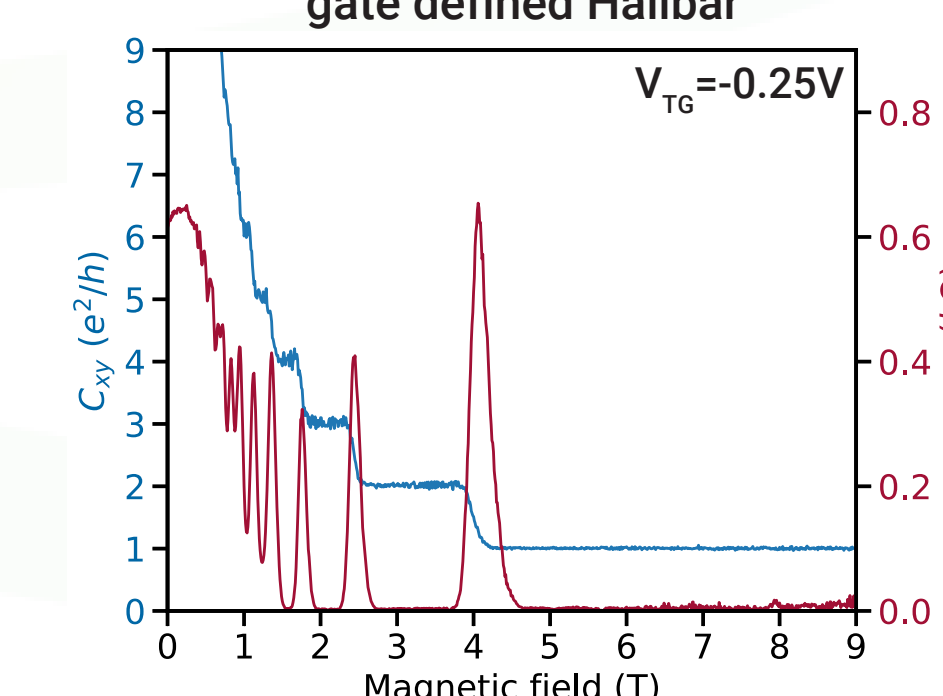
Hallbar with screening gates and identical dimensions to the one used



Conductance plateaus in screening gate defined Hallbar



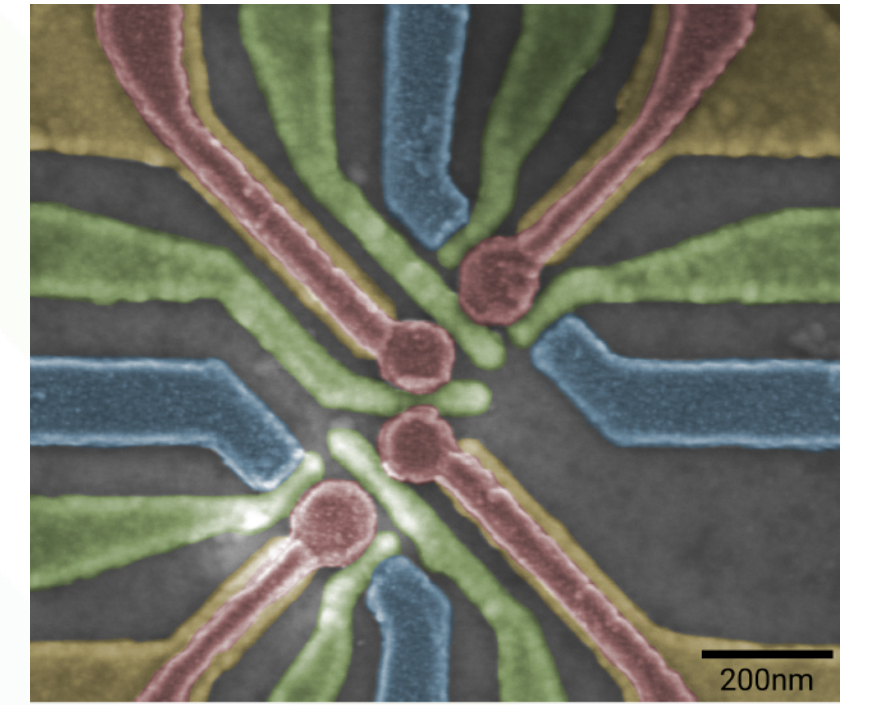
Mobility vs carrier density showing an increase in carrier density until  $V_{tg} = -0.1V$  following a drop at constant  $\mu$



Linecut through Landau fan showing quantized conductance and Shubnikov-de-Haas oscillations

## QUANTUM DOT SAMPLES

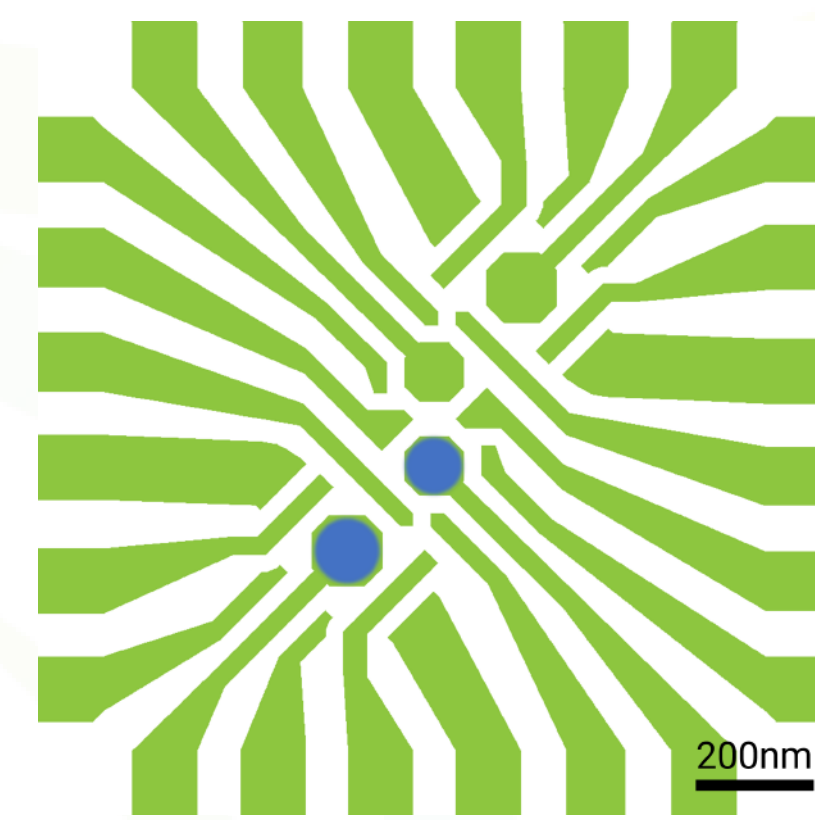
- Single layer devices for faster device and wafer iterations
- Two layer devices in fabrication for improved electrostatic control
- DQDs as initial device layout to establish qubits
- Qubits as a tool to investigate g-factor<sup>[4]</sup> and spin orbit interaction<sup>[5]</sup>



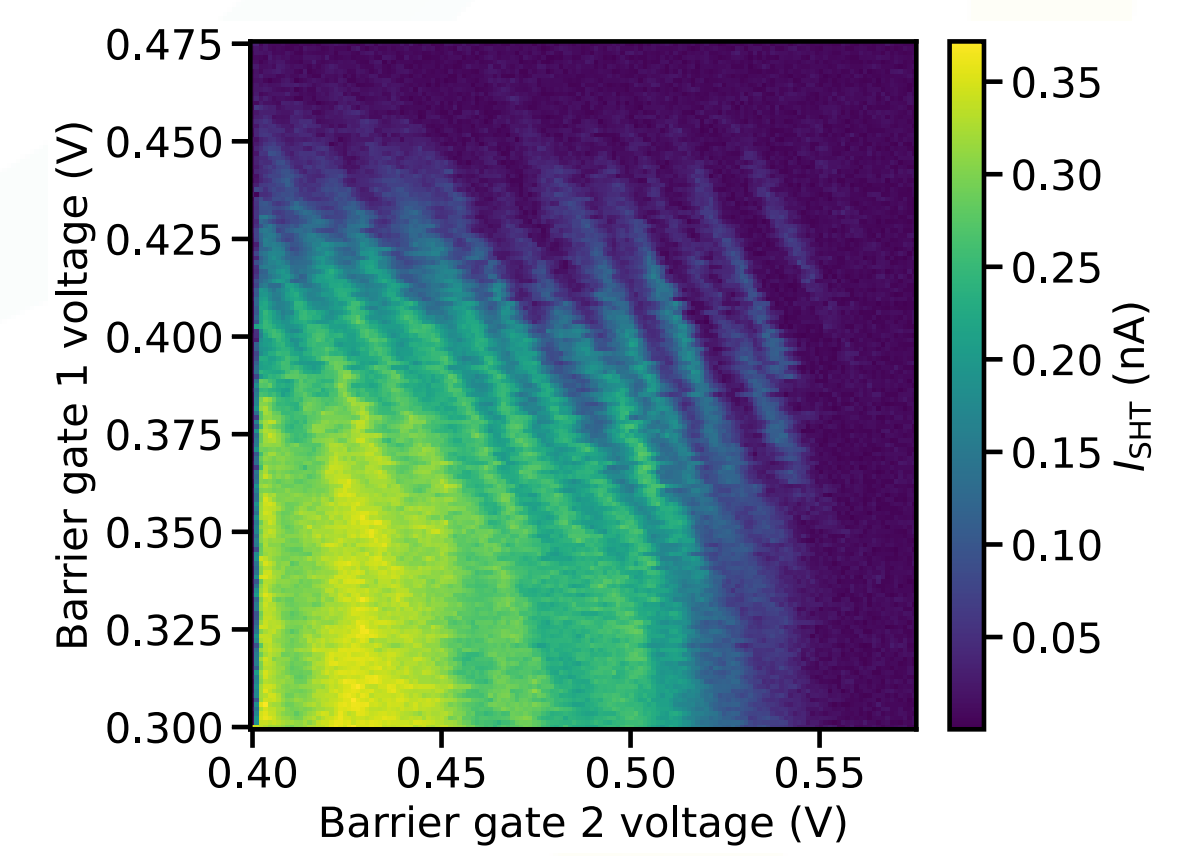
False colored SEM micrograph of a two layer device

## QUANTUM DOT MEASUREMENTS

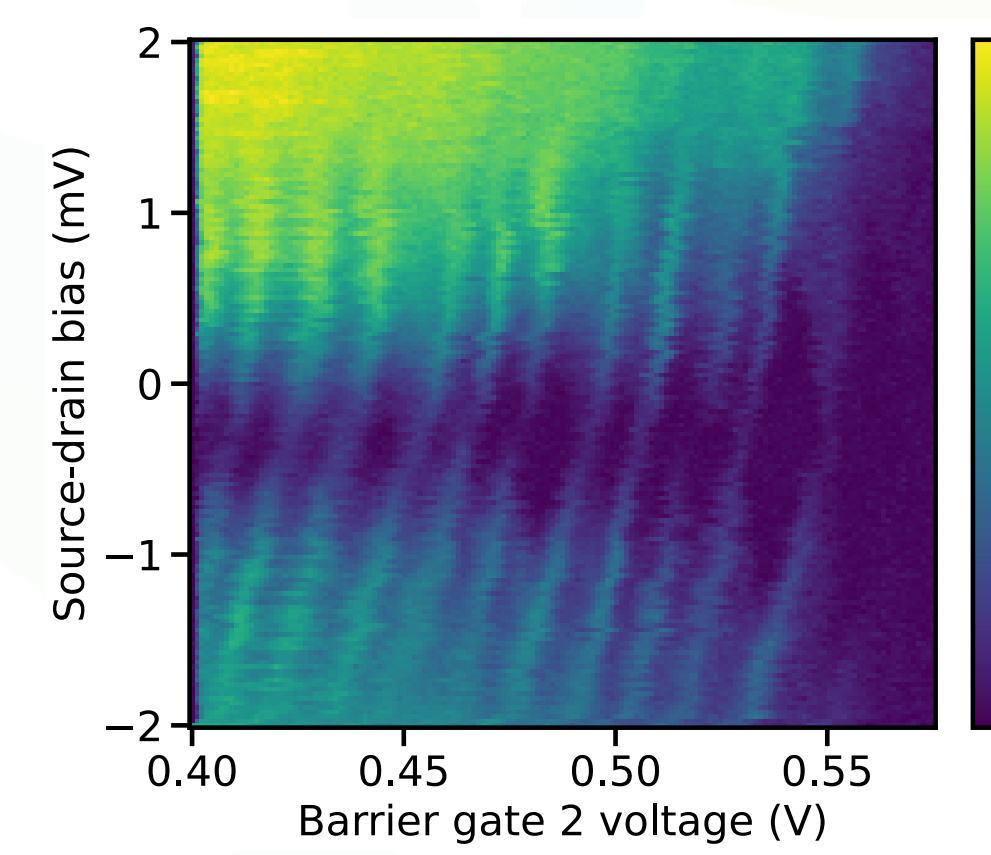
- Wafers require depletion mode quantum dots (wafer 1 used below)
- Well controllable sensing dot
- Both individual quantum dots formable
- DQD limited by interdot barrier formation in depletion mode wafer



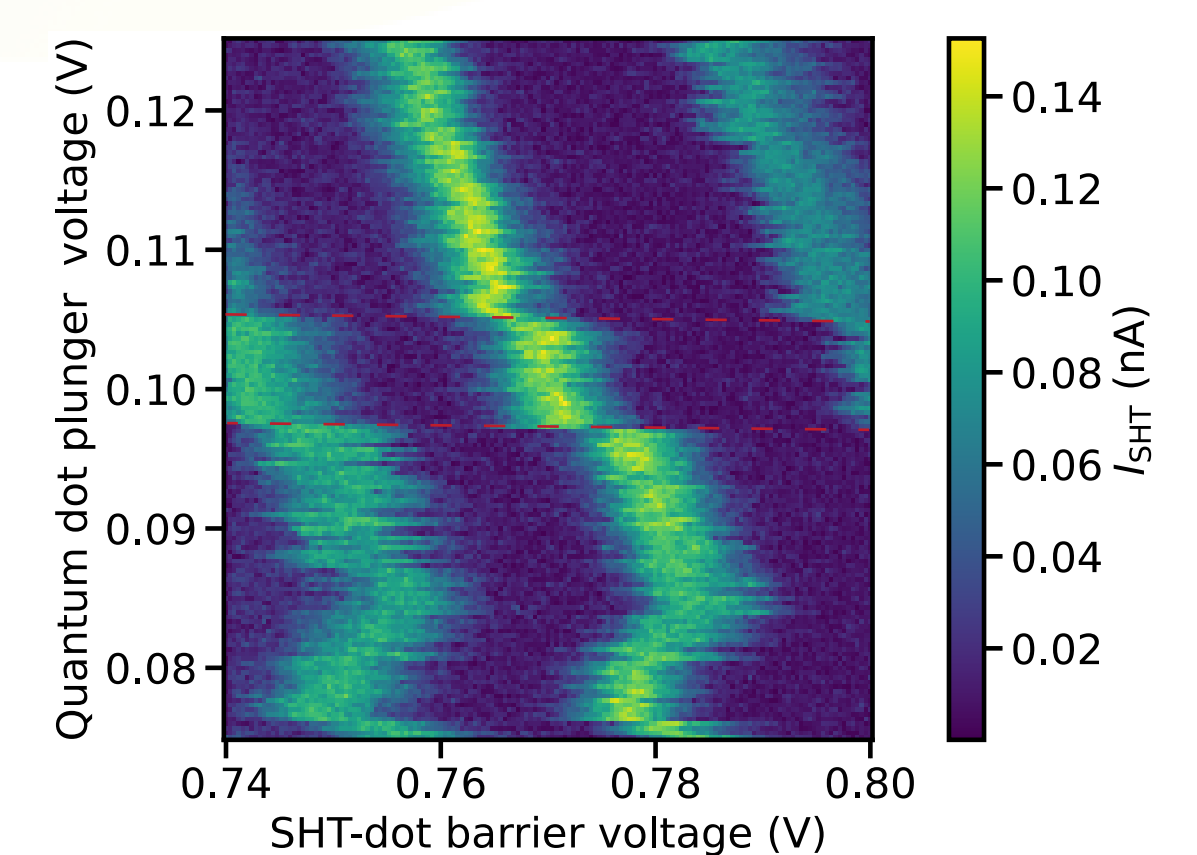
Gate layout of single layer devices used to measure an SHT and neighboring quantum dot



Single hole transistor barrier-barrier sweep



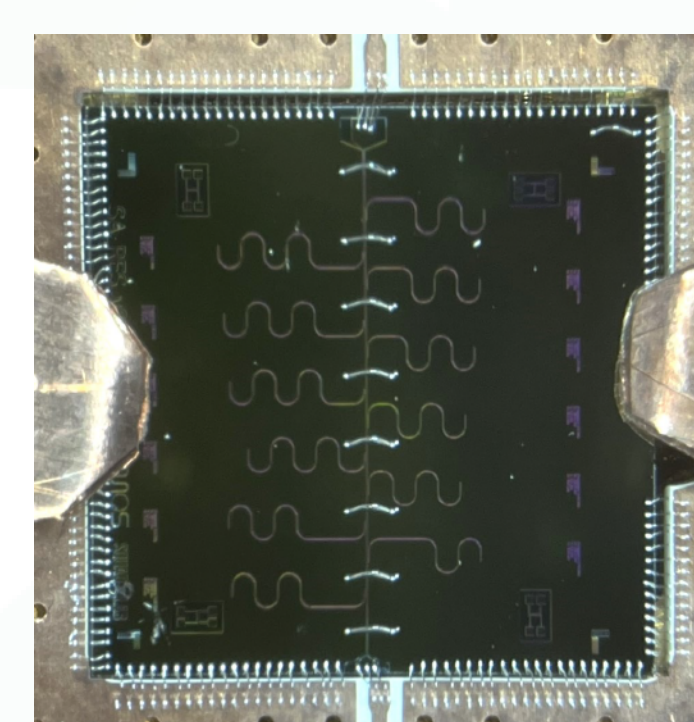
Coulomb diamonds in single hole transistor



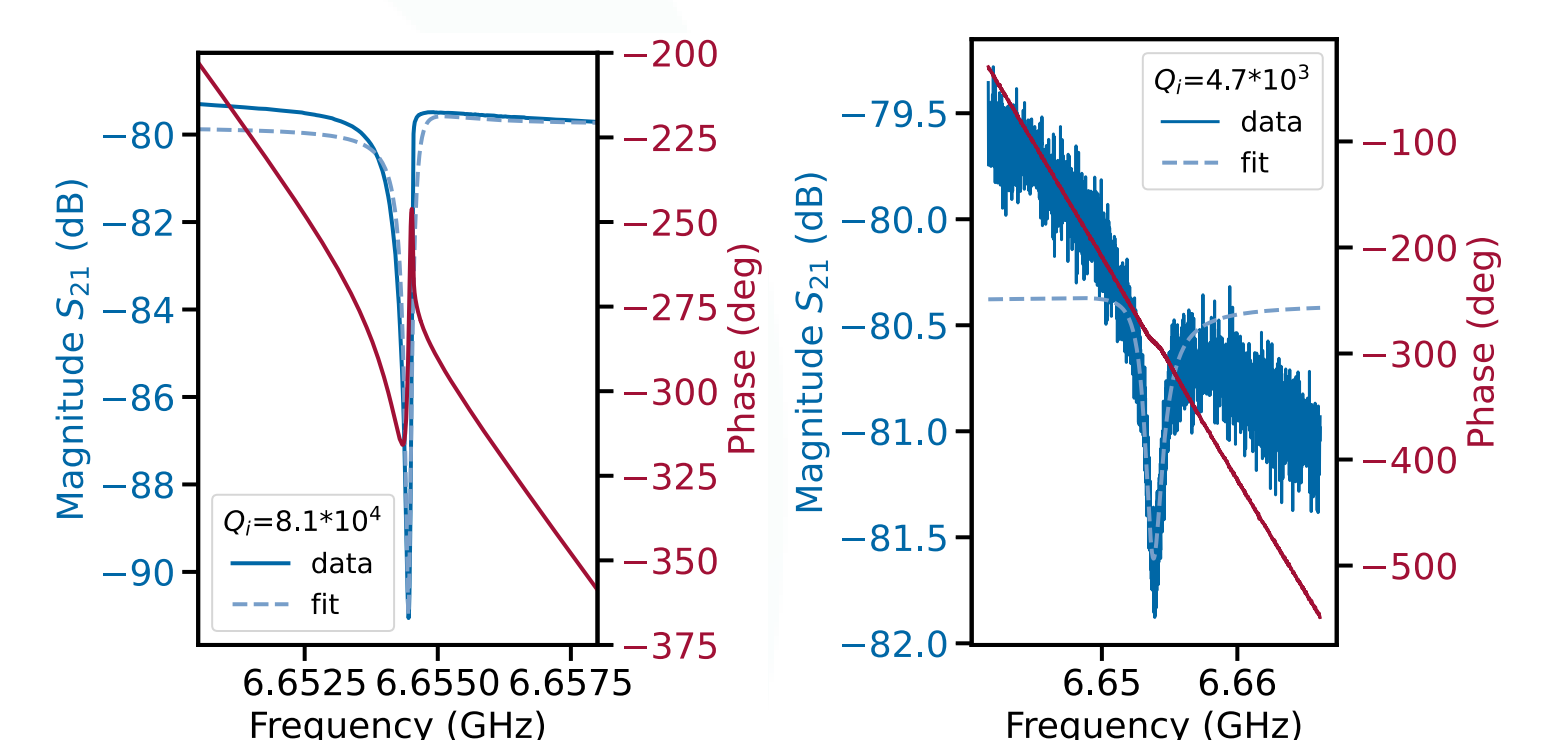
Charge sensing of a neighboring quantum dot dashed lines as visual guide

## RESONATORS ON GERMANIUM

- NbTiN resonators on Ge/SiGe with resonance frequencies between 5.5-7.5GHz
- Single photon quality factor  $Q_p \approx 5 \times 10^3$ , high power quality factor  $Q_h \approx 8 \times 10^4$



Mounted resonator sample. Stripline is connected to 12 quarterwave resonators at different frequency



NbTiN resonator on wafer 1 with extracted quality factors at input powers of -55dB and -130dB

## OUTLOOK AND REFERENCES

- Magnet inside ADR shields for co-integration of superconducting circuits and spin qubits
- Characterize g-factor tensor with Germanium spin qubits
- Measure spin-orbit interaction with spin qubits and in super-semi devices

- [1] Albrecht, W., Moers, J. & Hermanns, B. JLSRF 3, A112 (2017)  
[2] Bergen, A. et al., Rev. Sci. Instrum. 87, 105109 (2016)  
[3] Barends, R. et al., Appl. Phys. Lett. 99, 113507 (2011)  
[4] Sarker, A. et al. Phys. Rev. B 108, 245301 (2023)  
[5] Bulaev, D. and Loss, D. Phys. Rev. Lett. 98, 097202 (2007)